

• General Description

It combines advanced SGT MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

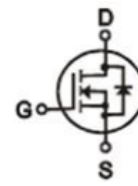
• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Oring switches
- Power Tools

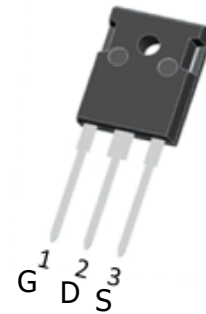
• Product Summary



$V_{DS} = 70V$

$R_{DS(ON)} = 1.4m\Omega$

$I_D = 350A$



TO-247

• Ordering Information:

Part NO.	ZM015N07HC
Marking	ZM015N07H
Packing Information	Bulk Tube
Basic ordering unit (pcs)	450

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	70	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ TC=25^\circ C$	350	A
	$I_D @ TC=75^\circ C$	266	A
	$I_D @ TC=100^\circ C$	220	A
Pulsed Drain Current ^①	I_{DM}	1050	A
Total Power Dissipation	$P_D @ TC=25^\circ C$	500	W
Total Power Dissipation	$P_D @ TA=25^\circ C$	4.2	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy @ $L=0.5mH$	E_{AS}	5000	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	0.29	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	30	° C/W
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	70			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0		4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 0.8 * BV_{DSS}$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 50A$		1.40	1.80	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 10A$		80		s
Source-drain voltage	V_{SD}	$I_S = 50A$			1.2	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1MHz$	-	19500	-	pF
Output capacitance	C_{oss}		-	1860	-	
Reverse transfer capacitance	C_{rss}		-	900	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	380	-	nC
Gate - Source charge	Q_{gs}	$I_D = 8A$	-	80	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	105	-	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20A,$ $di/dt = 100A/\mu s$		130		nS
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20A,$ $di/dt = 100A/\mu s$		450		nC

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

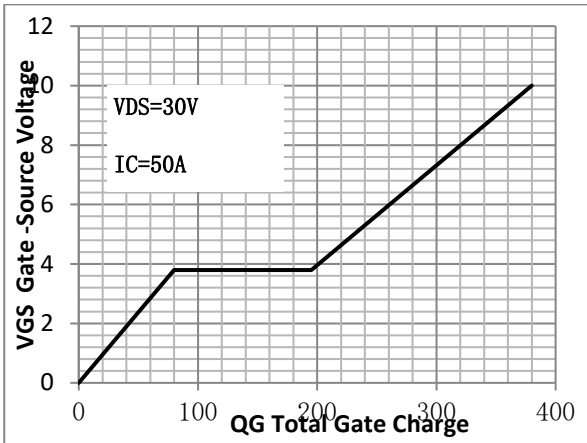


Fig.2 Capacitance Characteristics

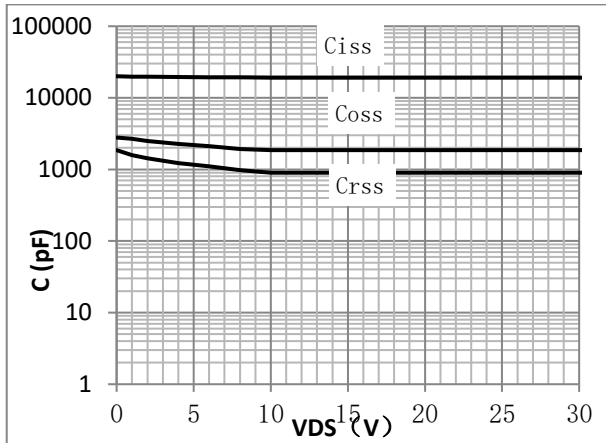


Fig.3 Power Dissipation

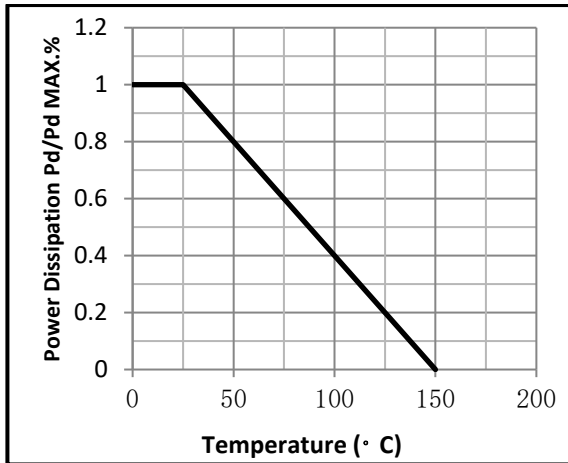


Fig.4 Typical output Characteristics

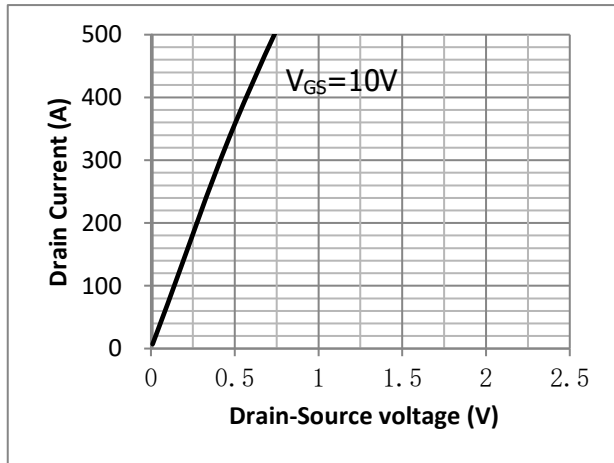


Fig.5 Threshold Voltage V.S Junction Temperature

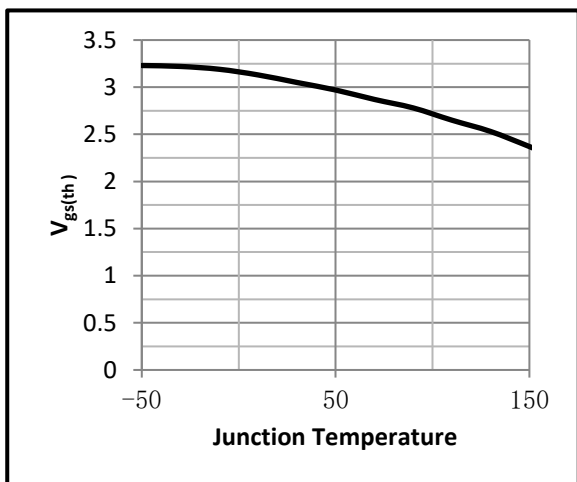


Fig.6 Resistance V.S Drain Current

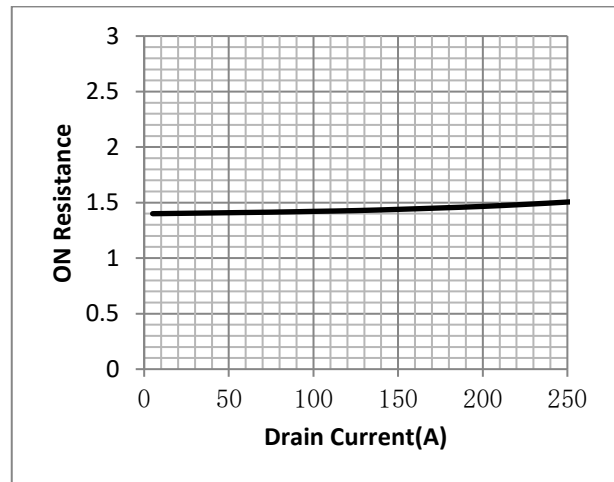


Fig.7 On-Resistance VS Gate Source Voltage

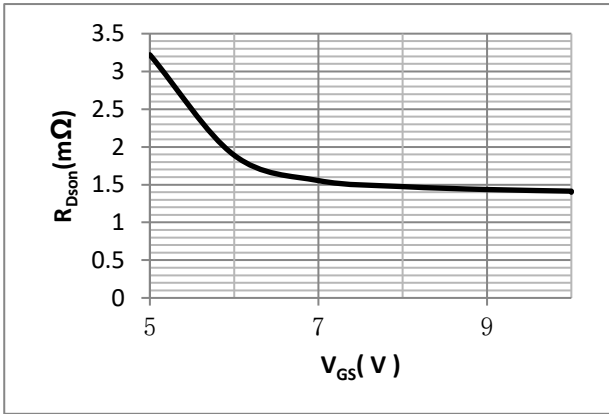


Fig.8 On-Resistance V.S Junction Temperature

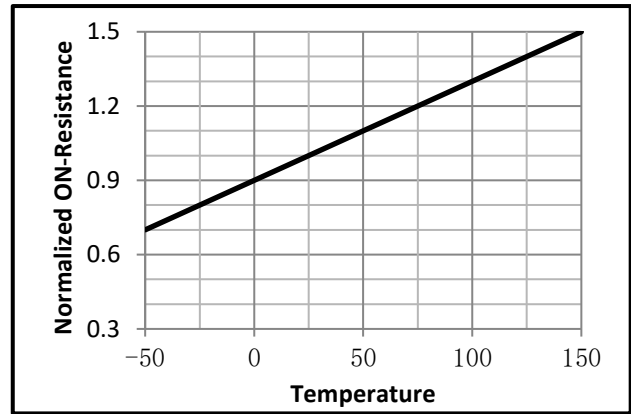


Fig.9 SOA Maximum Safe Operating Area

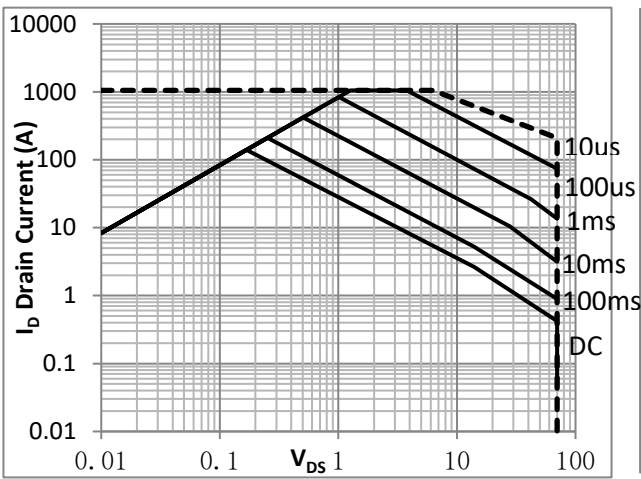


Fig.10 I_D -Junction Temperature

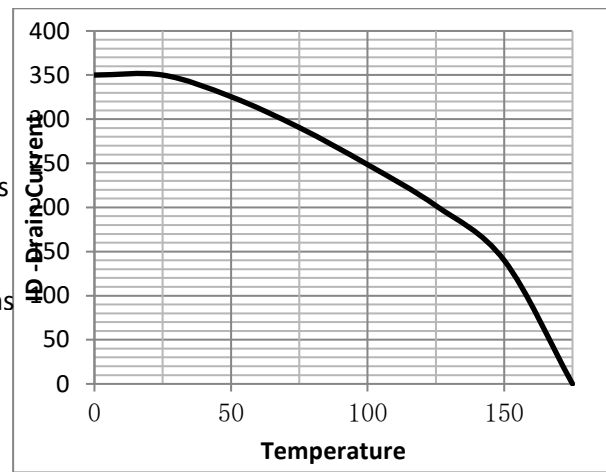


Fig.11 Switching Time Measurement Circuit

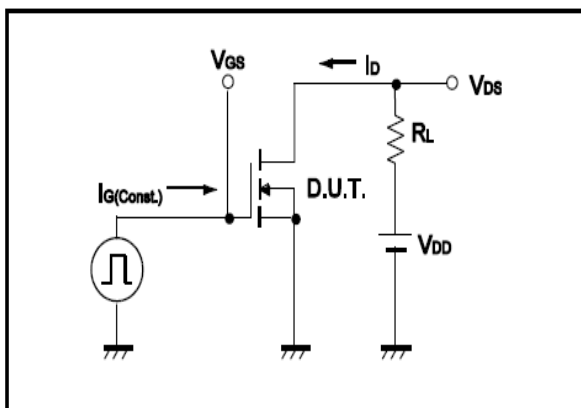


Fig.12 Gate Charge Waveform

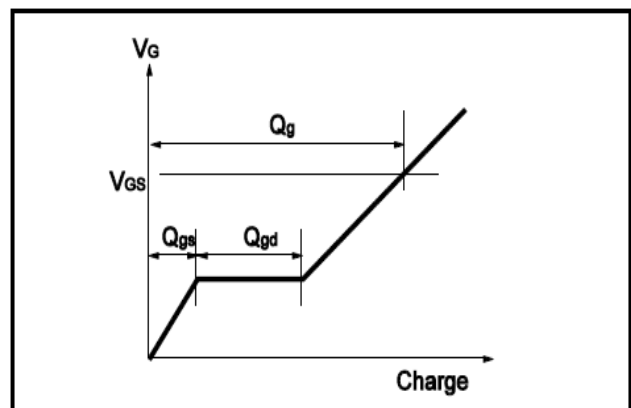


Fig.13 Switching Time Measurement Circuit

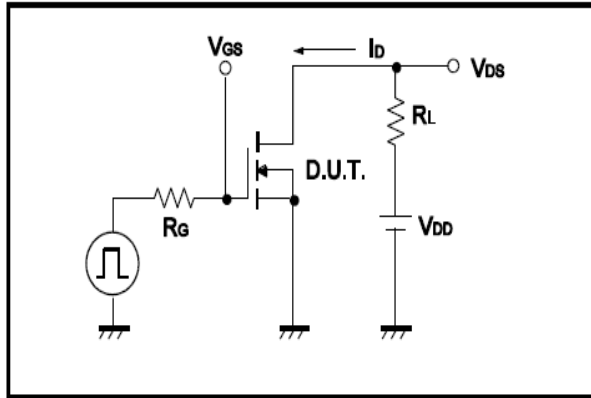


Fig.14 Gate Charge Waveform

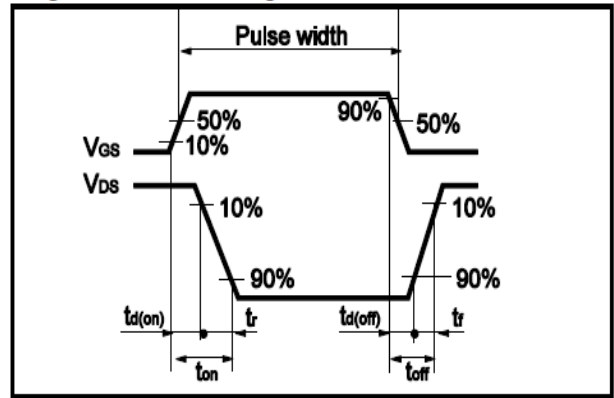


Fig.15 Avalanche Measurement Circuit

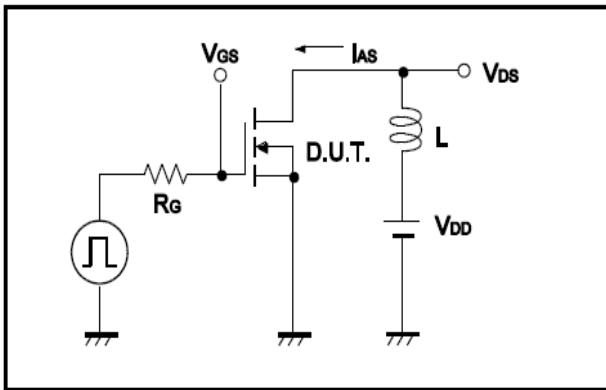
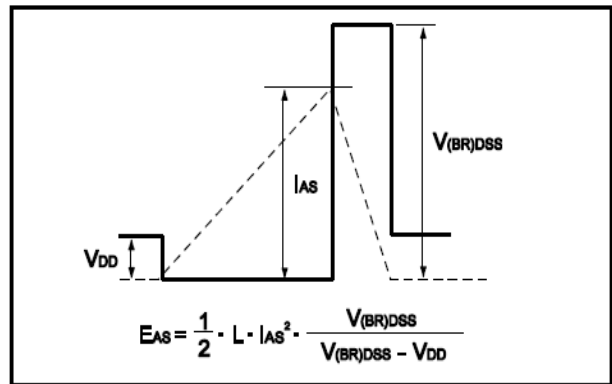
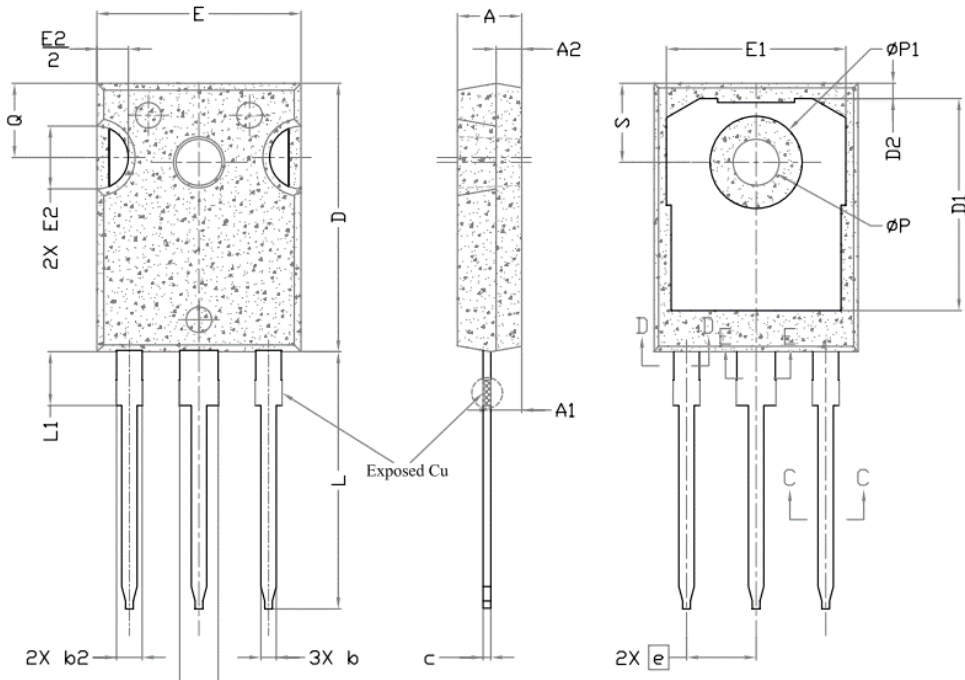


Fig.16 Avalanche Waveform





•Dimensions (TO-247)



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	